

UNISONIC TECHNOLOGIES CO., LTD

UDF015N07

Preliminary

Power MOSFET

0.15A, 70V N-CHANNEL DEPLETION-MODE POWER MOSFET

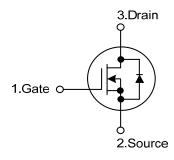
■ DESCRIPTION

The UTC **UDF015N07** is an N-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed.

■ FEATURES

- * $R_{DS(ON)} \le 16 \Omega$ @ $V_{GS}=0V$, $I_D=100mA$
- * Depletion Mode (Normally On)
- * Proprietary Advanced Planar Technology
- * Rugged Polysilicon Gate Cell Structure
- * Fast Switching Speed

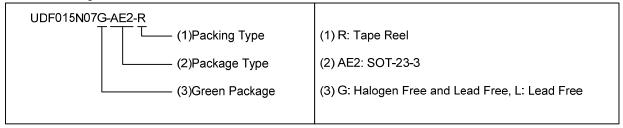
■ SYMBOL



ORDERING INFORMATION

Ordering Number		Daalaasa	Pin	Daaliaa			
Lead Free	Halogen Free	Package	1	2	3	Packing	
UDF015N07L-AE2-R	UDF015N07G-AE2-R	SOT-23-3	G	S	D	Tape Reel	

Note: Pin Assignment: G: Gate S: Source D: Drain



■ MARKING



ing igh 2 1 SOT-23-3 (JEDEC TO-236)

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■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Note 2)		V_{DSX}	70	V
Drain-Gate Voltage (Note 2)		V_{DGX}	70	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I _D	0.15	Α
	Pulsed	I _{DM}	0.3	Α
Power Dissipation		P _D	0.3	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	416	°C/W	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV_DSX	$I_D = 250 \mu A, V_{GS} = -30 V$	70			V	
Drain-Source Leakage Current		I _{D(OFF)}	V _{DS} =70V, V _{GS} =-30V			1	μΑ	
Gate-Source Leakage Current	Forward	I _{GSS}	V_{GS} =+30V, V_{DS} =0V			+100	nA	
	Reverse		V_{GS} =-30V, V_{DS} =0V			-100	nA	
ON CHARACTERISTICS								
Gate to Source Cut Off Voltage		$V_{GS(OFF)}$	V _{DS} =20V, I _D =8.0μA			-10	V	
Drain-Source Leakage Current		I _{DSS}	V_{DS} =25V, V_{GS} =0V	150			mΑ	
Static Drain-Source On-State Resistance		R _{DS(ON)}	V_{GS} =0V, I_D =100mA			16	Ω	
DYNAMIC PARAMETERS								
Input Capacitance		C _{ISS}			1.5		pF	
Output Capacitance		Coss	V _{GS} =-15V, V _{DS} =25V, f=1.0MHz		7.3		pF	
Reverse Transfer Capacitance		C_{RSS}			2.3		pF	
SWITCHING PARAMETERS								
Turn-ON Delay Time		$t_{D(ON)}$			32		ns	
Rise Time		t_R	V _{GS} =-15~0V, V _{DD} =30V,		36		ns	
Turn-OFF Delay Time		$t_{D(OFF)}$	$I_D=150$ mA, $R_G=20\Omega$		32		ns	
Fall-Time		t _F			34		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward Voltage		V_{SD}	I _{SD} =150mA, V _{GS} =-10V			1.4	V	

Notes: 1. Repetitive rating, pulse width limited by maximum junction temperature.

^{2.} T_J=+25°C ~ +150°C

^{2.} Pulse width \leq 380µs; duty cycle \leq 2%.

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